

Amended Claims

1. (withdrawn) A LVTSCR-like structure having one or more diodes formed in a p-well of the structure.
2. (currently amended) A method of increasing the holding voltage of an LVTSCR structure that includes an n-well and a p-well formed in a substrate, an n⁺ region and a p⁺ region formed in the n-well to define a high voltage node and an n⁺ region and a p⁺ region formed in the p-well to define a low voltage node, the method comprising forming at least one additional p⁺ region and at least one additional n⁺ region inside the p-well of the structure to define at least one p-n junction between the p-type material of the p-well and ~~any one of the~~ additional p⁺ regions in the p-well on the one hand, and the n-type material of ~~at least one of any one of the~~ additional n⁺ regions in the p-well on the other hand, the p-n junction being forward biased during normal operation by having said p⁺ region of the ~~defined~~ p-n junction located closer to ~~on the~~ high voltage node than the side of said at least one n⁺ region of the ~~defined~~ p-n junction.
3. (previously presented) A method of increasing the holding voltage of an LVTSCR structure having an anode in an n-well and a cathode in a p-well, the cathode being defined by an n⁺ region and a p⁺ region, comprising
forming at least one additional n⁺ region and at least one additional p⁺ region in the p-well to define at least one forward biased diode under normal operation in the p-well, thereby providing an alternative current path from anode to cathode through said at least one diode.
4. (original) A method of claim 3, wherein the alternative current path defines a lower resistance current path than the p-well.
5. (canceled)
6. (canceled)
7. (canceled)
8. (canceled)